

isc N-Channel MOSFET Transistor

IPP111N15N3, IIPP111N15N3

• FEATURES

- Static drain-source on-resistance: R_{DS}(on) ≤11.1mΩ
- · Enhancement mode
- · Fast Switching Speed
- · 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

DESCRITION

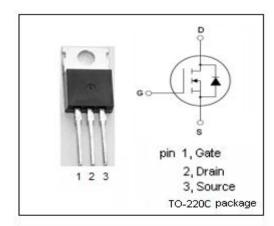
· Ideal for high-frequency switching and synchronous rectification

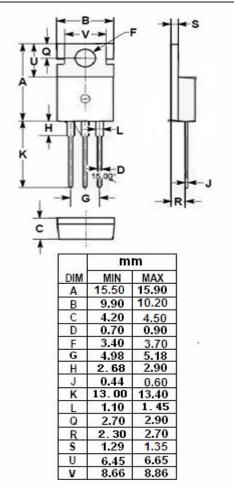
• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
$V_{ extsf{DSS}}$	Drain-Source Voltage	150	V
V _{GS}	Gate-Source Voltage	±20	V
I _D	Drain Current-Continuous	83	А
I _{DM}	Drain Current-Single Pulsed	332	А
P _D	Total Dissipation @T _C =25℃	214	W
Tj	Max. Operating Junction Temperature 175		$^{\circ}\mathbb{C}$
T _{stg}	Storage Temperature	-55~175	${\mathbb C}$

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT	
Rth(ch-c)	Channel-to-case thermal resistance	0.7	°C/W	
Rth(ch-a)	th(ch-a) Channel-to-ambient thermal resistance		°C/W	







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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	ТҮР	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D =1mA	150			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} ; I _D =160 μ A	2		4	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; I _D =83A			11.1	mΩ
I _{GSS}	Gate-Source Leakage Current	V _{GS} = 20V;V _{DS} =0V			0.1	μА
I _{DSS}	Drain-Source Leakage Current	V _{DS} =120V; V _{GS} = 0V			1	μА
V _{SD}	Diode forward voltage	I _F =83A; V _{GS} = 0V			1.2	V

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